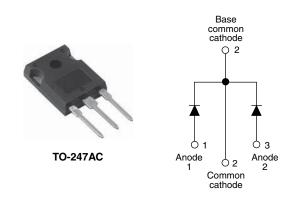
Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 2 x 6 A



PRODUCT SUMMARY								
Package	TO-247AC							
I _{F(AV)}	2 x 6 A							
V _R	1200 V							
V _F at I _F	3.0 V							
t _{rr} (typ.)	26 ns							
T _J max.	150 °C							
Diode variation	Single die							

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified for industrial level

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA12PA120CPbF is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. The VS-HFA12PA120CPbF has basic ratings of 1200 V and 6 A per leg continuous current. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA12PA120CPbF is ideally suited for applications in power supplies and power conversion systems (such as inverters, converters, UPS systems, and power factor correction circuits), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V _R		1200	V					
Maximum continuous forward current	1_	T _C = 100 °C	6						
per device	IF	$1_{\rm C} = 100$ C	12	А					
Single pulse forward current	I _{FSM}		80	A					
Maximum repetitive forward current	I _{FRM}		24						
Maximum power dissipation	р	T _C = 25 °C	62.5	W					
	P _D	T _C = 100 °C	25	vv					
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C					

 Document Number: 94597
 For technical questions

 Revision: 23-May-11
 DiodesAmericas@vishay.

For technical questions within your region, please contact one of the following: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> This document is subject to change without notice.

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COMPLIANT





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HEXFRED[®] Ultrafast Soft Recovery Diode, 2 x 6 A

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	1200	-	-				
		I _F = 6 A	-	2.7	3.0	v			
Maximum forward voltage	V _{FM}	I _F = 12 A -		3.5	3.9				
		I _F = 6 A, T _J = 125 °C	-	2.4	2.8				
Maximum reverse		$V_{R} = V_{R}$ rated	-	0.26	5.0				
leakage current	I _{RM}	T_J = 125 °C, V_R = 0.8 x V_R rated	-	110	500	μA			
Junction capacitance	CT	V _R = 200 V	-	9.0	14	pF			
Series inductance L _S		Measured lead to lead 5 mm from package body	-	8.0	-	nH			

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 $^{\circ}$ C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200$	A/μs, V _R = 30 V	-	26	-			
Reverse recovery time	t _{rr1}	T _J = 25 °C		-	53	80	ns		
	t _{rr2}	T _J = 125 °C		-	87	130			
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.4	8.0	A		
Feak recovery current	I _{RRM2}	T _J = 125 °C	I _F = 6 A	-	5.0	9.0			
Reverse recovery charge	Q _{rr1}	T _J = 25 °C	dI _F /dt = 200 A/μs V _R = 200 V	-	116	320			
neverse recovery charge	Q _{rr2}	T _J = 125 °C		-	233	585	ne		
Peak rate of fall of recovery	dl _{(rec)M} /dt1	T _J = 25 °C		-	180	-	A∕µs		
current during t _b	dl _{(rec)M} /dt2	T _J = 125 °C		-	100	-	γγµs		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	R _{thJC}		-	-	2.0				
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	K/W			
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.50	-				
Weight			-	2.0	-	g			
weight			-	0.07	-	oz.			
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)			
Marking device		Case style TO-247AC (JEDEC)	HFA12PA120C						

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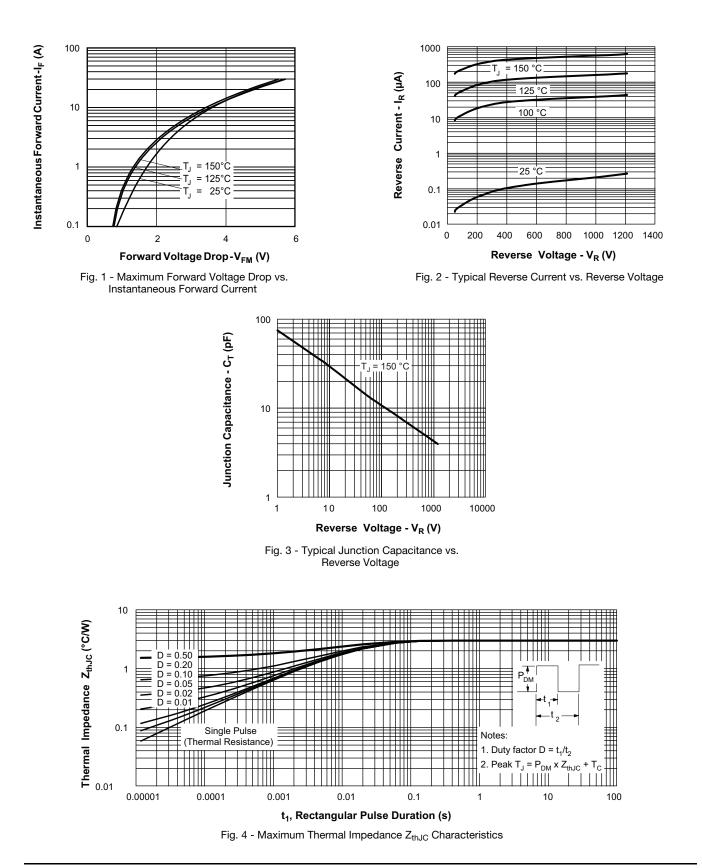
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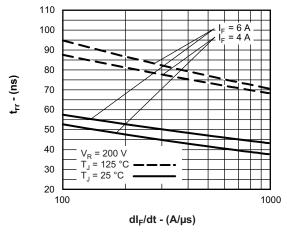
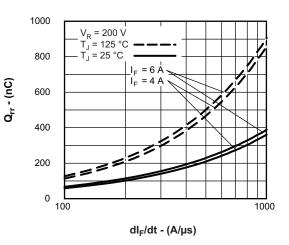


Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt



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Fig. 7 - Typical Stored Charge vs. dl_F/dt

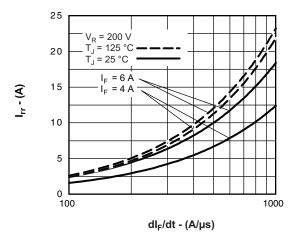


Fig. 6 - Typical Recovery Current vs. dl_F/dt

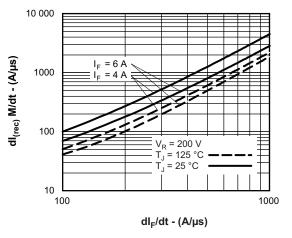


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

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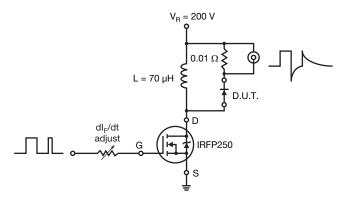


Fig. 9 - Reverse Recovery Parameter Test Circuit

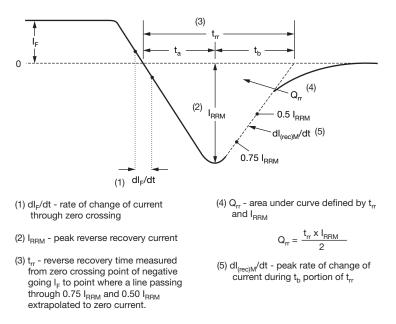
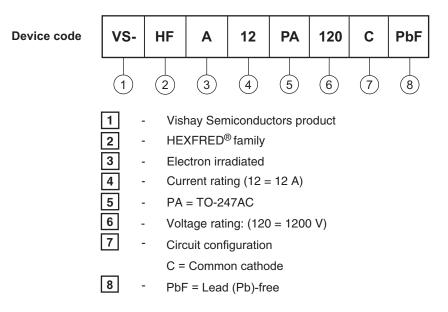


Fig. 10 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE



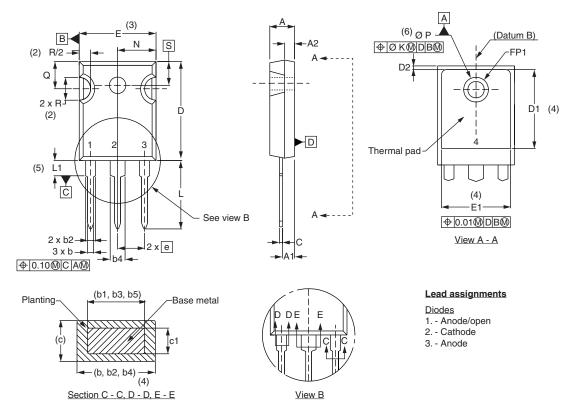
LINKS TO RELATED DOCUMENTS								
Dimensions	www.vishay.com/doc?95223							
Part marking information	www.vishay.com/doc?95226							

Outline Dimensions





DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		MILLIMETERS INCHES NOTES		SYMBOL	MILLIN	IETERS	INC	HES	NOTES		
STNIBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STWDOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.65	5.31	0.183	0.209			D2	0.51	1.30	0.020	0.051	
A1	2.21	2.59	0.087	0.102			E	15.29	15.87	0.602	0.625	3
A2	1.50	2.49	0.059	0.098			E1	13.72	-	0.540	-	
b	0.99	1.40	0.039	0.055			е	5.46	BSC	0.215	BSC	
b1	0.99	1.35	0.039	0.053			FK	2.	54	0.0)10	
b2	1.65	2.39	0.065	0.094			L	14.20	16.10	0.559	0.634	
b3	1.65	2.37	0.065	0.094			L1	3.71	4.29	0.146	0.169	
b4	2.59	3.43	0.102	0.135			Ν	7.62	BSC	0	.3	
b5	2.59	3.38	0.102	0.133			ΦР	3.56	3.66	0.14	0.144	
с	0.38	0.86	0.015	0.034			Φ P1	-	6.98	-	0.275	
c1	0.38	0.76	0.015	0.030			Q	5.31	5.69	0.209	0.224	
D	19.71	20.70	0.776	0.815	3]	R	4.52	5.49	1.78	0.216	
D1	13.08	-	0.515	-	4		S	5.51	BSC	0.217	BSC	

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁴⁾ Thermal pad contour optional with dimensions D1 and E1

⁽⁵⁾ Lead finish uncontrolled in L1

(6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

⁽⁷⁾ Outline conforms to JEDEC outline TO-247 with exception of dimension c

Revision: 16-Jun-11

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